

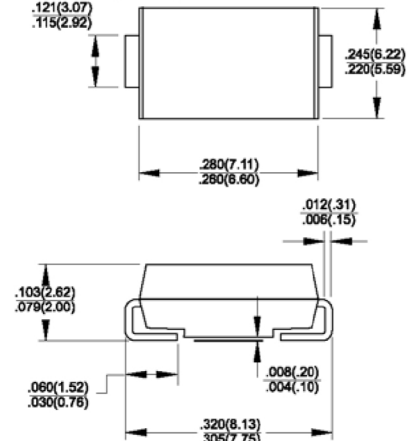
### Features

- ◆ Glass passivated junction chip
- ◆ For surface mounted application
- ◆ Low profile package
- ◆ Built-in strain relief
- ◆ Ideal for automated placement
- ◆ Easy pick and place
- ◆ Superfast recovery time for high efficiency
- ◆ Glass passivated chip junction
- ◆ High temperature soldering:  
250°C/10 seconds at terminals
- ◆ Plastic material used carries Underwriters Laboratory  
Classification 94V-O

### Mechanical Data

- ◆ Cases: Molded plastic
- ◆ Terminals: Solder plated
- ◆ Polarity: Indicated by cathode band
- ◆ Weight: 0.007 ounce, 0.21 gram

### DO-214AB (SMC)



Dimensions in inches and (millimeters)

### Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Parameter	Symbols	ES 3A	ES 3B	ES 3C	ES 3D	ES 3F	ES 3G	ES 3J	ES 3K	ES 3M	Units	
Maximum repetitive peak reverse voltage	$V_{RRM}$	50	100	150	200	300	400	600	800	1000	Volts	
Maximum RMS voltage	$V_{RMS}$	35	70	105	140	210	280	420	560	700	Volts	
Maximum DC blocking voltage	$V_{DC}$	50	100	150	200	300	400	600	800	1000	Volts	
Maximum average forward rectified current See Fig. 1	$I_{AV}$						3.0					Amps
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) @ $T_J=100^\circ\text{C}$	$I_{FSM}$						100.0					Amps
Maximum instantaneous forward voltage @ 3.0A	$V_F$	0.95			1.3			1.7			Volts	
Maximum DC reverse current @ $T_A=25^\circ\text{C}$ at rated DC blocking voltage @ $T_A=100^\circ\text{C}$	$I_R$						10.0 500					$\mu\text{A}$ $\mu\text{A}$
Maximum reverse recovery time (Note 1)	$t_r$						35					nS
Typical junction capacitance (Note 2)	$C_J$	50					40					pF
Typical thermal resistance (Note 3)	$R_{\theta JA}$ $R_{\theta JL}$						47 12					$^\circ\text{C}/\text{W}$
Operating junction temperature range	$T_J$						-55 to +150					$^\circ\text{C}$
Storage temperature range	$T_{STG}$						-55 to +150					$^\circ\text{C}$

**Notes:** 1. Reverse Recovery Test Conditions:  $I_F=0.5\text{A}$ ,  $I_R=1.0\text{A}$ ,  $I_{RR}=0.25\text{A}$

2. Measured at 1 MHz and Applied  $V_R=4.0$  Volts

3. Units Mounted on P.C.B. with 0.31 x 0.31" (8.0

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

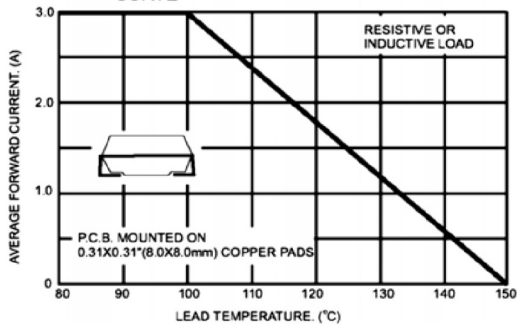


FIG.2- MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

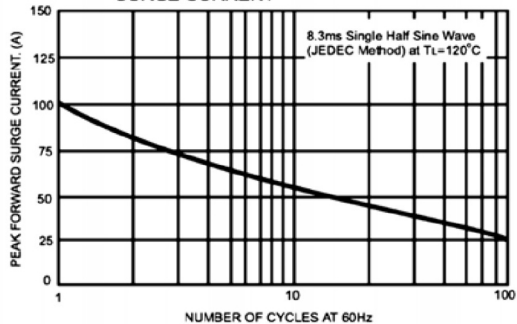


FIG.3- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

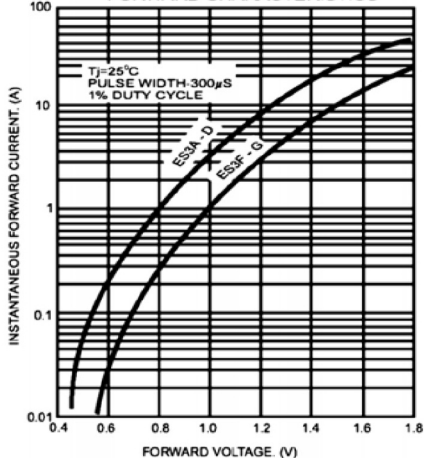


FIG.4- TYPICAL REVERSE CHARACTERISTICS

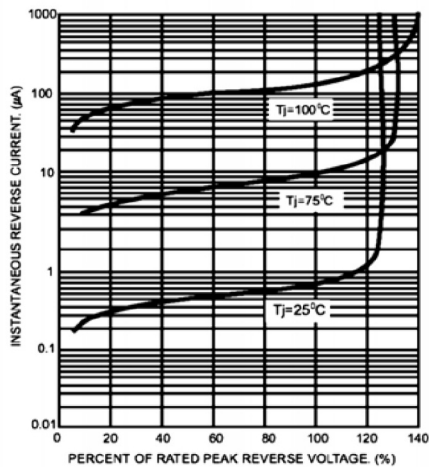
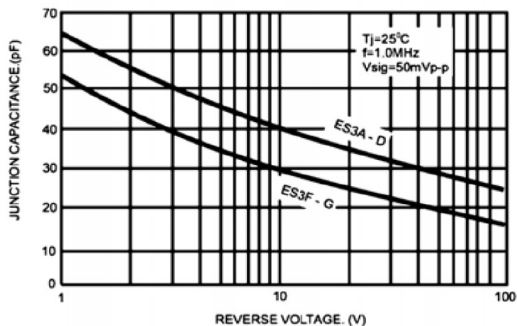


FIG.5- TYPICAL JUNCTION CAPACITANCE



单击下面可查看定价，库存，交付和生命周期等信息

[>>RCD\(达标电子\)](#)